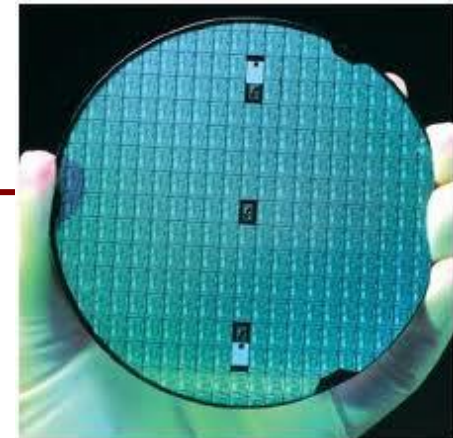
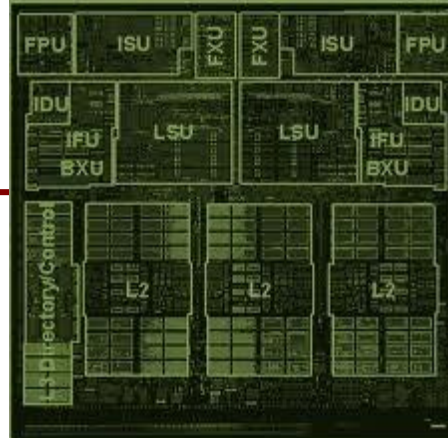
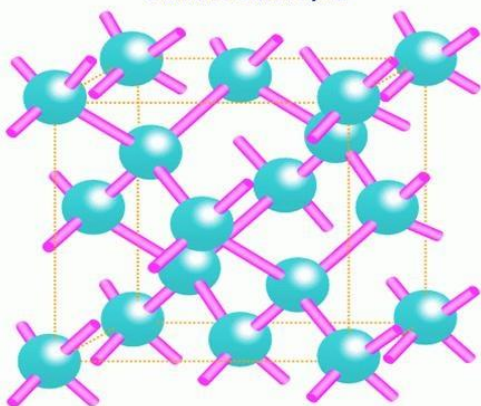


Structure of silicon crystal



ECE 225

Lecture 12

Power Dissipation in Nanoscale ICs

Prof. Kaustav Banerjee

Electrical and Computer Engineering

University of California, Santa Barbara

Forms of Power Dissipation

- **Dynamic Power**

- Due to charging/discharging of capacitors....

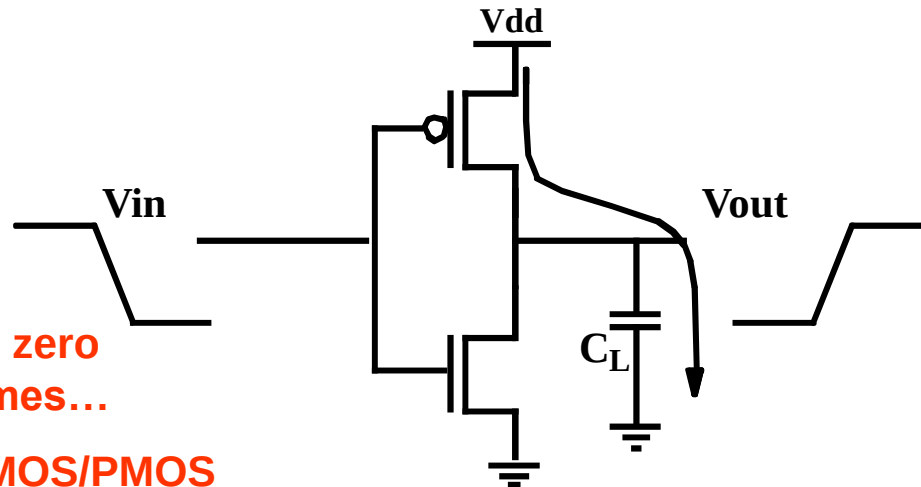
- **Leakage Power**

- Subthreshold leakage
- Gate leakage
- Junction leakage
- other mechanisms...DIBL, GIDL

- **Short-Circuit Power**

- When NMOS and PMOS are both turned ON....

Dynamic Power Dissipation



$$\text{Energy/transition} = C_L * V_{dd}^2$$

Low-to-High transition:

- C_L is charged through PMOS and discharged through NMOS
- During charging, voltage of C_L rises from 0 to V_{dd} ... energy is drawn from the power supply
- Part of this energy is stored in C_L while rest gets dissipated in the PMOS

Note: Here C_L is an external capacitor....

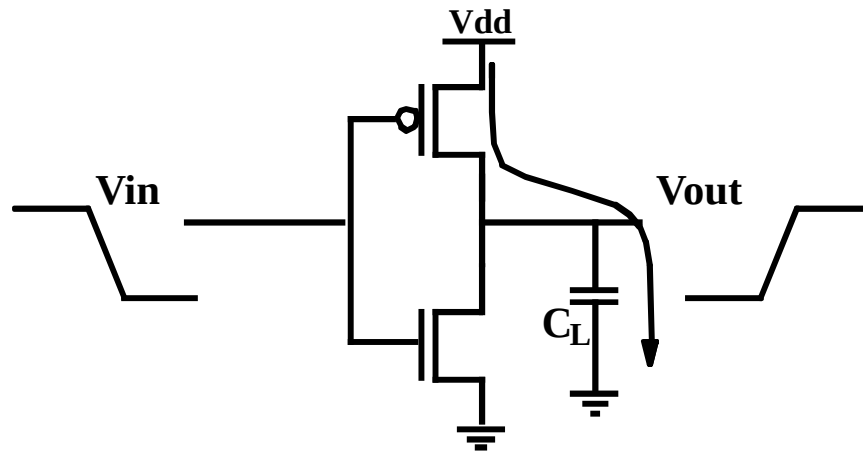
Energy/transition is not a function of transistor sizes!

- Need to reduce C_L , V_{dd} , and f to reduce power.

Energy taken from supply during transition:

$$E_{V_{DD}} = \int_0^{\infty} i_{V_{DD}}(t) V_{DD} dt = V_{DD} \int_0^{\infty} C_L \frac{dv_{out}}{dt} dt = C_L V_{DD} \int_0^{V_{DD}} dv_{out} = C_L V_{DD}^2$$

Dynamic Power Dissipation



High-to-Low transition:

- During the discharge phase, charge is removed from C_L and its energy is dissipated in the NMOS
- Each switching cycle consists of a L-H and H-L transition and takes a fixed amount of energy = $C_L V_{dd}^2$

Energy taken from supply during transition:

$$E_{V_{DD}} = \int_0^{\infty} i_{V_{DD}}(t) V_{DD} dt = V_{DD} \int_0^{\infty} C_L \frac{dv_{out}}{dt} dt = C_L V_{DD} \int_0^{V_{DD}} dv_{out} = C_L V_{DD}^2$$

Energy stored in the capacitor:

$$E_C = \int_0^{\infty} i_{V_{DD}}(t) v_{out} dt = \int_0^{\infty} C_L \frac{dv_{out}}{dt} v_{out} dt = C_L \int_0^{V_{DD}} v_{out} dv_{out} = \frac{C_L V_{DD}^2}{2}$$

Where is the other half of the energy?Dissipated in the PMOS

Dynamic Power Dissipation

$$\text{Power} = \text{Energy/transition} * f = C_L * V_{dd}^2 * f$$

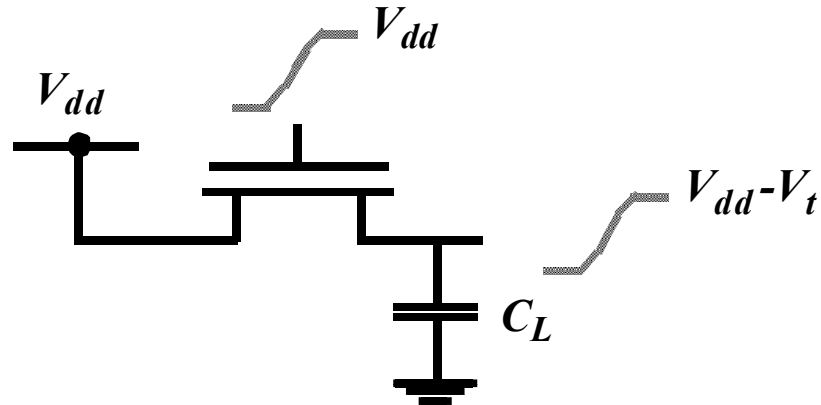
- “f” accounts for how often the gate is switched ON and OFF...
- f increases with scaling...since gate delay decreases

Consider a 0.25 um CMOS technology with a clock-rate of 500 MHz and average load capacitance of 15 fF/gate assuming a fan-out of 4: the power consumption per gate = 50 μ W (for $V_{dd} = 2.5$ V)

One-million such gates would result in a power consumption of 50W! (fortunately, not all gates are switching at the clock frequency...)

Power dissipation in a complex gate is more complex to estimate...since the switching frequency depends on the nature and statistics of the input signals. This is accommodated by replacing “f” with “p.F”, where p is the probability that a clock event results in a 0 to 1 transition and F is the maximum possible event-rate (or clock rate) of inputs

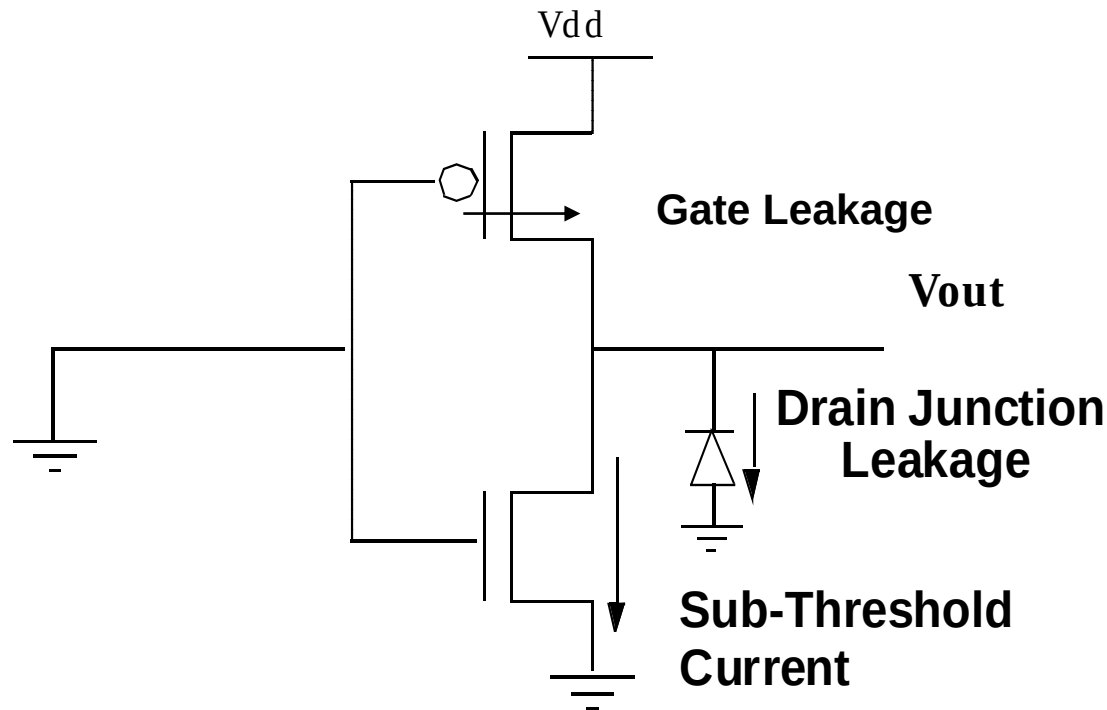
Modification for Circuits with Reduced Swing



$$E_{0 \rightarrow 1} = C_L \cdot V_{dd} \cdot (V_{dd} - V_t)$$

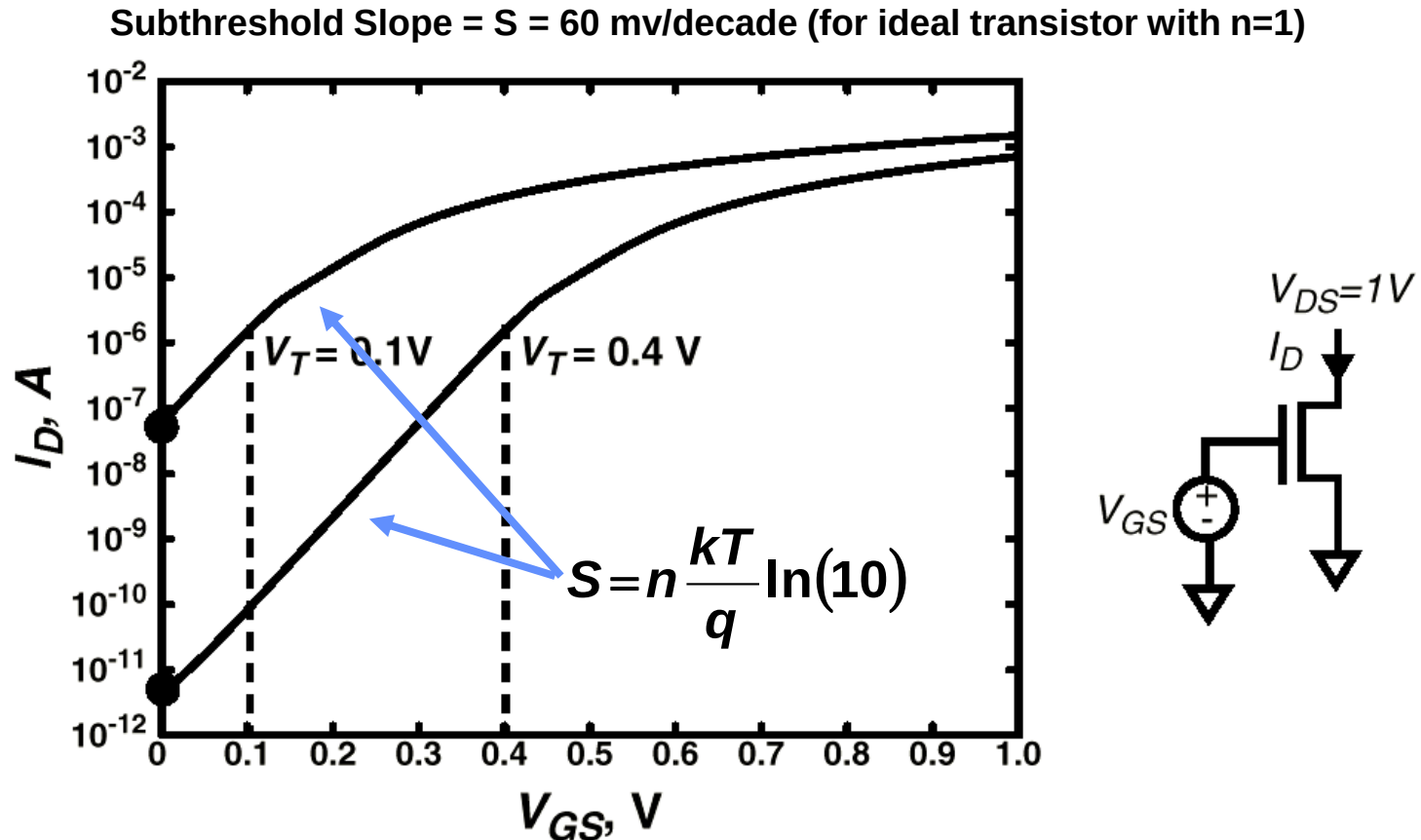
- Can exploit reduced swing to lower power (e.g., reduced bit-line swing in memory)

Primary Leakage Mechanisms



**Sub-threshold current one of most compelling issues
in low-power and energy-efficient circuit design!**

Subthreshold Leakage Component

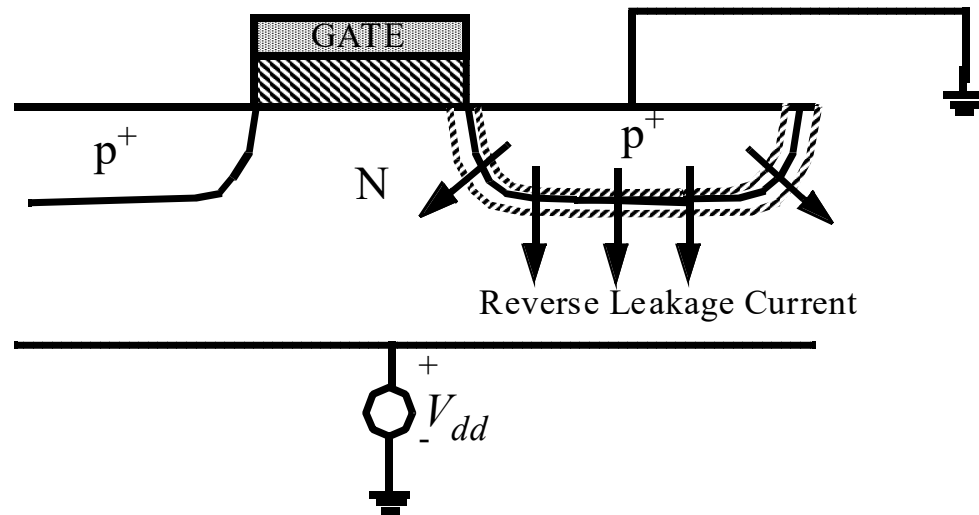


- Leakage control is critical for low-voltage operation

Note: DIBL will further increase subthreshold leakage!

Reverse-Biased Diode Leakage

Much smaller than
subthreshold
leakage.....

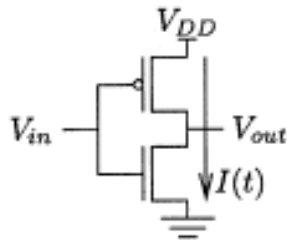


$$I_{DL} = J_S \times A$$

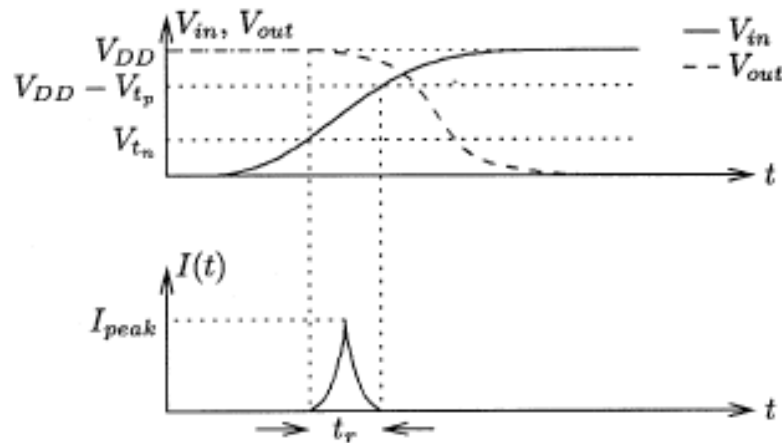
$J_S = 10\text{-}100 \text{ pA}/\mu\text{m}^2$ at 25 deg C for $0.25\mu\text{m}$ CMOS

J_S doubles for every 9 deg C!

Short Circuit Currents



(a)
CMOS
inverter.



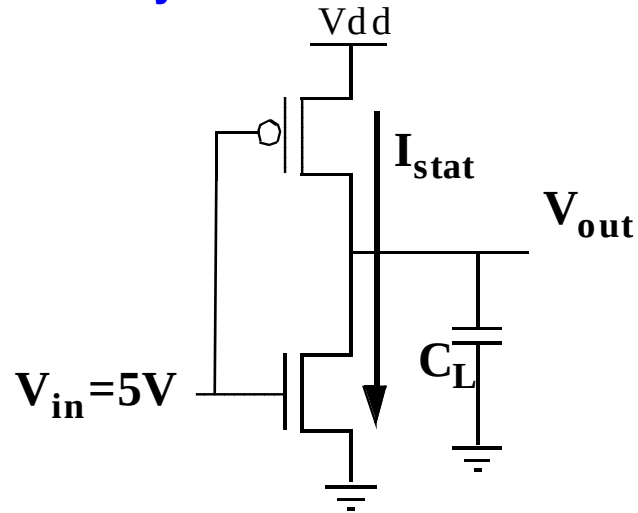
(b) Voltage and current waveforms.

K. Banerjee and A. Mehrotra, IEEE Transactions on
Electron Devices, Vol. 49, No. 11, 2002.

Fig. 5. Voltage and current waveforms of a CMOS inverter.

Static Power Consumption

In the absence of switching....steady-state operation



Sources:

Due to all previously mentioned leakage currents.....

$$P_{stat} = P_{(In=1)} \cdot V_{dd} \cdot I_{stat}$$

Wasted energy ...should be avoided in almost all cases...

Leakage Currents

□ Effect of leakage current

- “Wasted” power: power consumed even when circuit is inactive
- Leakage power raises temperature of chip – **positive feedback effect**
- Can cause functionality problem in some circuits: memory, dynamic logic, etc.

□ Reducing transistor leakage

- Long-channel devices
- Small drain voltage
- Large threshold voltage V_T

Leakage Power Reduction

□ Process scaling

- V_T reduces with each new process (historically)
- Leakage increases ~10X!

□ Leakage vs. performance tradeoff:

- For high-speed, need small V_T and L
- For low leakage, need high V_T and large L

□ One solution: dual- V_T process

- Low- V_T transistors: use in critical paths for high speed
- High- V_T transistors: use to reduce power

Principles for Power Reduction

☐ Prime choice: Reduce voltage!

- Dynamic power has quadratic dependence on V_{dd}
- Hard to reduce V_{dd} without reducing V_t
- Design at very low voltages (< 0.4 V) still open question
- Improve Subthreshold Swing to ~ 60 mV/decade
- Steep-slope transistors: such as TFET

☐ Reduce physical capacitance

- Device Sizing

☐ Reduce switching activity

- Exploit new architectures: Non Von-Neumann

What is the Lowest Possible Power Supply?

V_{dd} must be greater than a few times kT/q

Why is that?

For static CMOS, if minimum gain (near switching threshold) ≈ 1 , then $V_{dd,min} = (2-4) kT/q$

Refer to the derivation discussed in the class....

Consider effect of variability...